Notice of Allowability	Application No.	Applicant(s)
	10/713,220	ONISHI, TOSHIKAZU
	Examiner	Art Unit
	David Nhu	2818

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address--

All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. **THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS.** This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.

1. ☒ This communication is responsive to *11/17/03*.

2. ☒ The allowed claim(s) is/are *1-23*.

3. ☒ The drawings filed on *17 November 2003* are accepted by the Examiner.

4. ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
   a) ☒ All b) ☐ Some* c) ☐ None of the:
      1. ☒ Certified copies of the priority documents have been received.
      2. ☒ Certified copies of the priority documents have been received in Application No. *09/784,016* .
      3. ☐ Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)).

   * Certified copies not received: _____.

Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application.
THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.

5. ☐ A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.

6. ☐ CORRECTED DRAWINGS (as "replacement sheets") must be submitted.
   (a) ☐ including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached
      1) ☐ hereto or 2) ☐ to Paper No./Mail Date _____.
   (b) ☐ including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No./Mail Date _____.

   Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the header according to 37 CFR 1.121(d).

7. ☐ DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.

Attachment(s)

1. ☒ Notice of References Cited (PTO-892)
2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)
3. ☒ Information Disclosure Statements (PTO-1449 or PTO/SB/08), Paper No./Mail Date 01
4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material
5. ☐ Notice of Informal Patent Application (PTO-152)
6. ☐ Interview Summary (PTO-413), Paper No./Mail Date _____.
7. ☐ Examiner's Amendment/Comment
8. ☒ Examiner's Statement of Reasons for Allowance
9. ☐ Other _____.

REASONS FOR ALLOWANCE

1. Claims 1-23 are allowed.

2. The following is an examiner's statement of reasons for allowance: None of the references of record teaches or suggests as cited in claims 1, 7, 13, 19: A method for fabricating a semiconductor laser device, the semiconductor laser device comprising: a first semiconductor laminated structure which is provided on a front side region of a substrate and includes a first active layer for oscillating a first laser beam having a first wavelength band; and a second semiconductor laminated structure which is provided on a rear side region of the substrate and includes a second active layer for oscillating a second laser beam having a second wavelength band, the method comprising: growing a first tentative semiconductor laminated structure having the same laminated structure as the second semiconductor laminated structure on the substrate; removing a front side portion of the first tentative semiconductor laminated structure, thereby producing the second semiconductor laminated structure on the rear side region of the substrate; growing a second tentative semiconductor laminated structure having the same laminated structure as the first semiconductor laminated structure on the front side region of the substrate and on the second semiconductor laminated structure; removing a portion of the second tentative semiconductor laminated structure above the second semiconductor laminated structure, thereby producing the first semiconductor laminated structure on the front side region of the substrate (as cited in claim 1); growing a first tentative semiconductor laminated structure having the same laminated structure as the second semiconductor laminated structure on the substrate; removing a rear side portion of the first tentative semiconductor laminated structure, thereby producing the second semiconductor laminated

structure on the rear side region of the substrate; growing a second tentative semiconductor laminated structure having the same laminated structure as the first semiconductor laminated structure on the front side region of the substrate and on the second semiconductor laminated structure; removing a portion of the second tentative semiconductor laminated structure above the first semiconductor laminated structure, thereby producing the second semiconductor laminated structure on the rear side region of the substrate; (as cited in claim 7); providing a first laser chip including a first active layer for oscillating a first laser beam having a first wavelength band and a second laser chip including a second active layer for oscillating a second laser beam having a second wavelength band; fixing the first laser chip to a front side region of a substrate and fixing the second laser chip to a rear side region of the substrate, wherein the second step comprises the step of fixing the first laser chip and the second laser chip so that an emission direction of the first laser beam and an emission direction of the second laser beam are same (as cited in claim 13);); providing a first laser chip including a first active layer for oscillating a first laser beam having a first wavelength band and a second laser chip including a second active layer for oscillating a second laser beam having a second wavelength band, and a third laser chip including a third active layer for oscillating a third laser beam having a third wavelength band; fixing the first laser chip to a front side region of a substrate and fixing the second laser chip to a central region of the substrate, and fixing the third laser chip to a rear side region of the substrate, wherein the second step comprises the step of fixing the first laser chip and the second laser chip , and the third laser chip so that an emission direction of the first laser beam and an emission direction of the second laser beam, and an emission direction of the third laser beam are same (as cited in claim 19).

3. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

CONCLUSION

4. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure: Onishi (6,661,824 B2): Semiconductor Laser Device and Method for Fabricating the same.

5. Any inquiry concerning this communication on earlier communications from the examiner should be directed to David Nhu , (571)272-1792. The examiner can normally be reached on Monday-Friday from 7:30 AM to 5:00 PM.

The examiner's supervisor, David Nelms can be reached on (571)272-1787.

The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956

David Nhu

March 18, 2005

DAVID NHU
PRIMARY EXAMINER